

Wei Guo

List of Publications by Year in descending order

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17
papers

606
citations

840776

11
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888059

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17
docs citations

17
times ranked

661
citing authors

#	ARTICLE	IF	CITATIONS
1	Polarization modulation of 2DEG toward plasma-damage-free GaN HEMT isolation. Applied Physics Letters, 2022, 121, 012104.	3.3	6
2	Polarity Control and Nanoscale Optical Characterization of AlGaIn-Based Multiple-Quantum-Wells for Ultraviolet C Emitters. ACS Applied Nano Materials, 2020, 3, 5335-5342.	5.0	10
3	Polarity control and fabrication of lateral polarity structures of III-nitride thin films and devices: progress and prospects. Journal Physics D: Applied Physics, 2020, 53, 483002.	2.8	14
4	Revealing the surface electronic structures of AlGaIn deep-ultraviolet multiple quantum wells with lateral polarity domains. Photonics Research, 2020, 8, 812.	7.0	2
5	Lateral polarity control of III-nitride thin film and application in GaN Schottky barrier diode. Journal of Semiconductors, 2018, 39, 053003.	3.7	1
6	Tuning photonic crystal fabrication by nanosphere lithography and surface treatment of AlGaIn-based ultraviolet light-emitting diodes. Materials and Design, 2018, 160, 661-670.	7.0	18
7	Enhancing light coupling and emission efficiencies of AlGaIn thin film and AlGaIn/GaN multiple quantum wells with periodicity-wavelength matched nanostructure array. Nanoscale, 2017, 9, 15477-15483.	5.6	16
8	Fabrication and structural properties of AlN submicron periodic lateral polar structures and waveguides for UV-C applications. Applied Physics Letters, 2016, 108, .	3.3	32
9	KOH based selective wet chemical etching of AlN, Al _x Ga _{1-x} N, and GaN crystals: A way towards substrate removal in deep ultraviolet-light emitting diode. Applied Physics Letters, 2015, 106, .	3.3	66
10	Nanostructure surface patterning of GaN thin films and application to AlGaIn/AlN multiple quantum wells: A way towards light extraction efficiency enhancement of III-nitride based light emitting diodes. Journal of Applied Physics, 2015, 117, 113107.	2.5	29
11	Fermi level control of compensating point defects during metalorganic chemical vapor deposition growth of Si-doped AlGaIn. Applied Physics Letters, 2014, 105, 222101.	3.3	47
12	Stimulated emission and optical gain in AlGaIn heterostructures grown on bulk AlN substrates. Journal of Applied Physics, 2014, 115, .	2.5	56
13	The effect of polarity and surface states on the Fermi level at III-nitride surfaces. Journal of Applied Physics, 2014, 116, .	2.5	75
14	Properties of AlN based lateral polarity structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 261-264.	0.8	11
15	Comparative study of etching high crystalline quality AlN and GaN. Journal of Crystal Growth, 2013, 366, 20-25.	1.5	59
16	Lasing and longitudinal cavity modes in photo-pumped deep ultraviolet AlGaIn heterostructures. Applied Physics Letters, 2013, 102, .	3.3	104
17	Polarity control and growth of lateral polarity structures in AlN. Applied Physics Letters, 2013, 102, .	3.3	60